

AN 1987-196552 [28] WPIDS  
DNN N1987-147048 DNC C1987-082359  
TI Bonding wire for semiconductor device e.g. IC, LSI - comprises copper  
contg. sulphur matrix, and indium, magnesium, beryllium, **boron**,  
zirconium, silver, silicon, calcium etc..  
DC L03 M26 U11 X12  
PA (NIHA) NIPPON MINING CO; (TATD) TATSUTA DENSEN KK  
CYC 1  
PI JP 62127438 A 19870609 (198728)\* 5p  
JP 03079416 B 19911218 (199203)  
ADT JP 62127438 A JP 1985-265621 19851126; JP 03079416 B JP 1985-265621  
19851126  
PRAI JP 1985-265621 19851126  
AB JP 62127438 A UPAB: 19930922  
The bonding wire comprises Cu having 99.999  
wt.% or over purity, contg. 0.0005 wt.% or less S, as a matrix, to which  
as additive elements, less than 0.02 wt.% (A) In and Mg, as a total, and  
0.01 wt.% or less (B) at least one of Be, B, Zr, Y,  
Ag, Si, Ca, and rare earth elements, but 0.02 wt.% or less (A)+(B  
) groups, are added.  
USE - The bonding wire is used for connection between electrodes on  
semiconductor devices such as transistors, IC's, and LSI's, and outer  
leads. With the wire, heat resistance, fracture strength and bonding  
characteristics can be improved.  
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